

Table of Contents

Preface

Free-Standing 3C-SiC P-Type Doping by Al Ion Implantation

M. Canino, F. Torregrosa, M. Zielinski, V. Boldrini, C. Bidini, M. Russo, P. Maccagnani and F. La Via 1

TEM Investigation on High Dose Al Implanted 4H-SiC Epitaxial Layer

C. Calabretta, N. Piluso, C. Bongiorno, S. Boninelli, F. La Via and A. Severino 7

Evolution of the Substitutional Fraction on Post-Implantation Annealing in Al/4H-SiC Systems

V. Boldrini, A. Parisini and M. Pieruccini 13

Low Resistivity Aluminum Doped Layers Formed Using High Dose High Temperature Implants and Laser Annealing

F. Mazzamuto, Z. Chehadi, F. Roze, M. Opprecht, A. Gupta, S. Kerdilès, T. Tabata, M. Ameen, D. Roh, C. Sohl, M. Lazar, L.M. Rubin and L. Thuries 21

Improving HfO₂ Thick Films for SiC Power Devices by Si, Y and La Doping

S. Krause, T. Mikolajick and U. Schroeder 29

Dopant Activation Comparison in Phosphorus and Nitrogen Implanted 4H-Silicon Carbide

S. Das, D.J. Lichtenwalner, H. Dixit, S. Rogers, A. Scholze and S.H. Ryu 35

Transient-Enhanced Diffusion of Implanted Aluminum in 4H-SiC

K.L. Mletschnig, P.P. Michałowski and P. Pichler 41

Calibration of Aluminum Ion Implantation Monte-Carlo Model for TCAD Simulations in 4H-SiC

A. Scholze, A.V. Suvorov, D.J. Lichtenwalner, S. Rogers, H. Dixit and S.H. Ryu 47

Prediction of Contact Resistance of 4H-SiC by Machine Learning Using Optical Microscope Images after Laser Doping

Y. Iwaizumi, T. Yasunami, K. Katayama, Y. Kakimoto, D. Nakamura, T. Goto and H. Ikenoue 53

The Effect of Nitrogen Plasma Treatment Process on Ohmic Contact Formation to N-Type 4H-SiC

A.H.B.I.A. Yeo, V.Q.G. Roth, L.K. Bera, N. Singh, U. Chand, S. Chung, A. Ranjan, G. Ho, S.K. Lim and X. Gong 59

Ni/4H-SiC Ohmic Contact Formation Using Multipulse Nanosecond Laser Annealing

M. Opprecht, S. Kerdilès, J. Biscarrat, P. Godignon, C. Masante, R. Laviéville, N. Vaxelaire, P. Gergaud, A. Grenier, C. Jung, F. Roze, Z. Chehadi, L. Thuries, L. Lu and T. Tabata 65

Lift-Off Process for Patterning of a Sputter-Deposited Thick Metal Stack for High Temperature Applications on 4H-SiC

A. Fuchs, K. Brueckner, K. Ehrensberger and O. Rusch 71

Plasma Treatment after NiSi-Based Ohmic Contact Formation on 4H-SiC to Enhance Adhesion of Subsequent Backside Metallization

T. Becker, C. Hellinger, A. Fuchs, J. Koerfer and O. Rusch 79

Effect of Substrate Heating on Low Contact-Resistance Formation by Excimer Laser Doping for 4H-SiC

Y. Kakimoto, T. Yasunami, K. Katayama, D. Nakamura, T. Goto and H. Ikenoue 85

Nickel Ohmic Contacts Formed on 4H-SiC by UV Laser Annealing

J.F. Michaud, C. Berger and D. Alquier 91

Electrical and Structural Properties of Ohmic Contacts of SiC Diodes Fabricated on Thin Wafers

P. Badalà, C. Bongiorno, P. Fiorenza, G. Bellocchi, E. Smecca, M. Vivona, M. Zignale, M. Massimino, I. Deretzis, S. Rascunà, M. Frazzica, M. Boscaglia, F. Roccaforte, A. La Magna and A. Alberti 97

Empirical Model of Low-Ohmic Nickel-Based Contact Formation on N-Type 4H-SiC Depending on Thermal Budget

C. Hellinger, M. Rommel and A.J. Bauer 105

Low-Ohmic Nickel Contacts on N-Type 4H-SiC by Surface Roughness Dependent Laser Annealing Energy Density Optimization

C. Hellinger, M. Rommel and A.J. Bauer 113

Long Term Reliability and Deterioration Mechanisms of High-Temperature Metal Stacks on 4H-SiC	
K. Brueckner and O. Rusch	119
Metal Contact Processing Experiments towards Realizing 500 °C Durable RF 4H-SiC BJTs	
S. Rajgopal, D.J. Spry, D. Lukco and P.G. Neudeck	125
Performance Improvement by Carbon-Dioxide Supercritical Fluid Treatment for 4H-SiC Vertical Double Diffusion MOSFETs	
H.M. Chen, C.H. Yen, W.C. Hung, W.C. Hung, H.M. Kuo, F.C. Liang and T.C. Chang	131
Hydrogen Etching Process of 4H-SiC (0001) in Limited Regions	
A. Mancuso, S. Boninelli, M. Camarda, P. Fiorenza, A. Mio, V. Scuderi, P. Godignon, S. Aslanidou, L. Calcagno and F. La Via	137
Comparative Study of the Self-Aligned Channel Processes for 4H-SiC VDMOSFET	
J.T. Hsiao, C.L. Hung, Y.K. Hsiao and B.Y. Tsui	145
Demonstration of Low Interface Trap Density ($\sim 3 \times 10^{11} \text{eV}^{-1} \text{cm}^{-2}$) SiC/SiO₂ MOS Capacitor with Excellent Performance Using H₂+NO POA Treatment for SiC Power Devices	
U. Chand, L.K. Bera, N. Singh, T. Fidler, P. Schmid, S. Kumar, V.Q.G. Roth, A.H.B.I.A. Yeo, H. Cakmak, A. Ranjan, P. Vudumula, M. Camalleri, L. Scalia, M. Saggio, A. Guarnera, M.K. Teoh, M. Castorina and S. Chung	151
Increasing Mobility in 4H-SiC MOSFETs with Deposited Oxide by <i>In-Situ</i> Nitridation of SiC Surface	
M. Yakut, A. Roy, F. Arith, A. Whitworth, A. Alexander, J. Gryglewicz, J. Sheriff, S. Olsen, K. Vasilevskiy and A. O'Neill	157
Demonstrating SiC <i>In Situ</i> Rounded Trench Processing Technologies for Future Power Trench MOSFET Applications	
B. Jones, A. Croot, J. Mitchell, C. Bolton, J.E. Evans, F. Monaghan, K. Riddell, M. Jennings, O. Guy and H. Ashraf	163
High Mobility 4H-SiC P-MOSFET via Ultrathin ALD B₂O₃ Interlayer between SiC and SiO₂	
E.K. Ashik, V. Misra and B. Lee	171
Quality Improvement of SiC Substrate Surface with Using Non-Abrasive CMP Slurry	
S.J. Lee, B.H. Park, C.H. Lee, I.K. Lee, J.D. Seo, K.R. Ku, B.H. Choi, E.O. Kim, N.R. Shin, S.Y. Jung, D.W. Kim, J.H. Na and W.J. Lee	181
Addition of Transition Metal Ion CMP Slurry for Forming Ultra-Flat SiC Crystal	
S.H. Kim, H.S. Ryu, C.H. Lee, M.O. Kyun, J.D. Seo, K.R. Ku, J.W. Lee, B.H. Choi, E.O. Kim, N.R. Shin, S.Y. Jung, D.W. Kim, H.L. Lee, Y.J. Choi and W.J. Lee	187
Increasing 4H-SiC Trench Depth by Improving the Dry Etch Selectivity towards the Oxide Hard Mask	
O. Rusch, K. Brueckner and T. Erlbacher	193
A Comparison between Different Post Grinding Processes on 4H-SiC Wafers	
B. Cafra, A. Grasso, N. Piluso and A. Severino	201
Influence of Active Area Etching Method on the Integrity of Gate Oxide on 4H-SiC	
C.H. Wang, L.J. Lin, C.L. Hung, Y.K. Hsiao and B.Y. Tsui	211
High-K Gate Dielectric for High-Performance SiC Power MOSFET Technology with Low Interface Trap Density, Good Oxide Lifetime ($t_{\text{ddb}} \geq 10^4 \text{s}$), and High Thermal Stability ($\geq 800^\circ \text{C}$)	
U. Chand, L.K. Bera, N. Singh, C. Zhixian, S. Kumar, V.Q.G. Roth, A.H.B.I.A. Yeo, B. Varghese, P. Vudumula, H. Cakmak, A. Ranjan, L. Huamao and S. Chung	217